

Single Event Radiation Hardened Quad Voltage Comparators

IS-139ASRH, IS-139ASEH



The single event effects and total dose radiation hardened IS-139ASRH, IS-139ASEH consist of four independent single or dual supply voltage comparators on a single

monolithic substrate. The common mode input voltage range includes ground, even when operated from a single supply, and the low supply current makes these comparators suitable for low power applications. These types were designed to directly interface with TTL and CMOS inputs.

The IS-139ASRH, IS-139ASEH are fabricated on our dielectrically isolated Rad Hard Silicon Gate (RSG) process, which provides immunity to single event latch-up and the capability of highly reliable performance in any radiation environment.

Specifications for Rad Hard QML devices are controlled by the Defense Logistics Agency Land and Maritime (DLA). The SMD numbers listed below must be used when ordering.

Detailed Electrical Specifications for the IS-139ASRH, IS-139ASEH are contained in [SMD 5962-01510](#).

Features

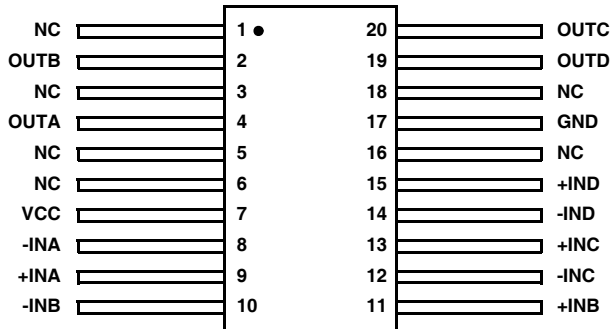
- Electrically Screened to SMD # 5962-01510
- QML Qualified per MIL-PRF-38535 Requirements
- Radiation Hardness
 - Total Dose 300krad(Si) (Max)
 - Single Event Latch-up >84MeV/mg/cm²
 - Single Event Upset >84MeV/mg/cm²
- Operating Supply Voltage Range 9V to 30V
- Input Offset Voltage (V_{IO}) 5mV (Max)
- Quiescent Supply Current 3mA (Max)
- Differential Input Voltage Range Equal to the Supply Voltage

Applications

- DC-DC Power Conversion
- Pulse Generators
- Timing Circuitry
- Level Shifting
- Analog to Digital Conversion

Pin Configuration

IS9-139ASRH, IS9-139ASEH
(FLATPACK CDFP4-F20)
TOP VIEW



Ordering Information

| ORDERING NUMBER | INTERNAL MKT. NUMBER | TEMP. RANGE (°C) | PACKAGE DRAWING NUMBER |
|-------------------|----------------------|------------------|------------------------|
| 5962F0151001VXC | IS9-139ASRH-Q | -55 to +125 | K20.A |
| 5962F0151001QXC | IS9-139ASRH-S | -55 to +125 | K20.A |
| 5962F0151002VXC | IS9-139ASEH-Q | -55 to +125 | K20.A |
| IS9-139ASRH/PROTO | IS9-139ASRH/PROTO | -55 to +125 | K20.A |

IS-139ASRH, IS-139ASEH

Die Characteristics

DIE DIMENSIONS

3750 μm x 4510 μm (148 mils x 178 mils)
483 μm \pm 25.4 μm (19 mils \pm 1 mil)

INTERFACE MATERIALS

Glassivation

Type: Silox (SiO₂)
Thickness: 8.0k Å \pm 1.0k Å

Top Metallization

Type: AlSiCu
Thickness: 16.0k Å \pm 2k Å

Substrate

Radiation Hardened Silicon Gate, Dielectric Isolation

Backside Finish

Silicon

ASSEMBLY RELATED INFORMATION

Substrate Potential

Unbiased (DI)

ADDITIONAL INFORMATION

Worst Case Current Density

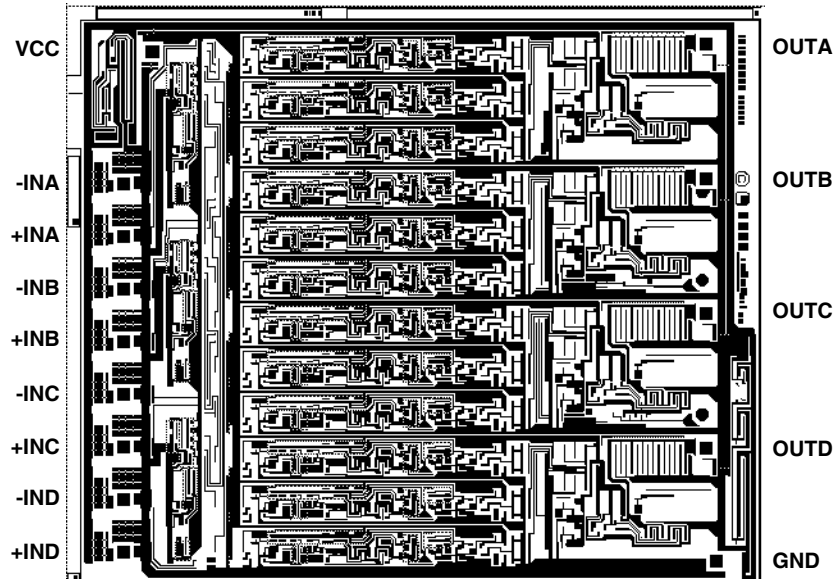
$<2.0 \times 10^5 \text{ A/cm}^2$

Transistor Count

644

Metallization Mask Layout

IS-139ASRH, IS-139ASEH



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